

# PWR-SMP400

## PWM Power Supply IC

### 20-100 VDC Input

### Isolated, Regulated DC Output



### Product Highlights

#### Integrated Power Switch and CMOS Controller

- Output power > 5 W from 48 VDC input
- Integrated solution minimizes overall size
- External transformer provides isolation and selectable output voltages

#### High-voltage, Low-capacitance MOSFET Output

- Designed for telecommunications and distributed power applications
- Low capacitance allows for high frequency operation

#### High-speed Voltage-mode PWM Controller

- Internal pre-regulator self-powers the IC on start-up
- High PWM frequency reduces component size
- Minimum external parts required

#### Built-In Self-protection Circuits

- Inherent current limiting protects from short circuits
- Input overvoltage shutdown/undervoltage lockout
- Thermal shutdown

## Description

The PWR-SMP400, intended for telecommunications and distributed power applications, combines a high voltage power MOSFET switch with a switchmode power system controller in a monolithic integrated circuit. Few external components are required to implement a low cost, isolated converter. High frequency operation reduces total power supply size.

The power MOSFET switch features include high voltage, low  $R_{DS(ON)}$ , low capacitance, and low gate threshold voltage. The combination of lower capacitance and lower gate threshold voltage results in a tenfold reduction in gate drive power. Lower capacitances also facilitate higher frequency operation.

The controller section of the PWR-SMP400 contains all the blocks required to drive and control the power stage: off-line start-up pre-regulator circuit, oscillator, bandgap reference, error amplifier, gate driver, undervoltage lockout, and over-temperature protection, and current limiting. This voltage-mode Pulse Width Modulation control circuit is optimized for flyback topologies.

The PWR-SMP400 is available in a 16-pin plastic batwing DIP or 20-pin batwing SOIC package.

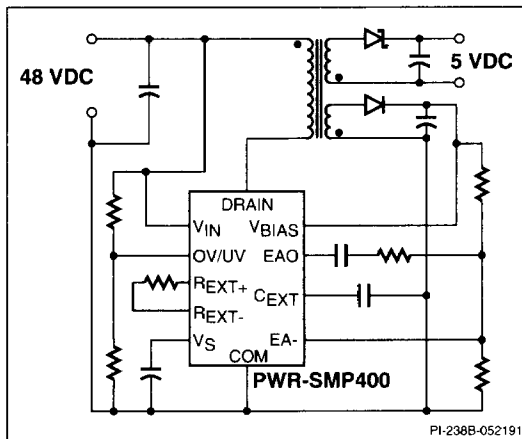


Figure 1. Typical Application

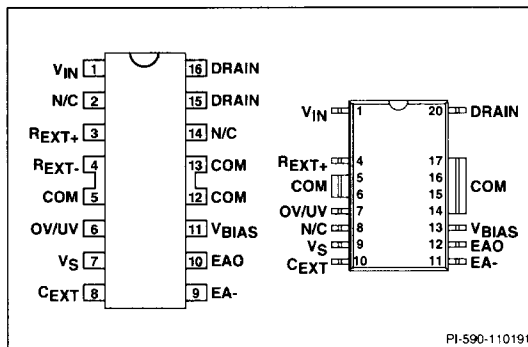


Figure 2. Pin Configurations.

### ORDERING INFORMATION

PART NUMBER	PACKAGE	TEMP RANGE
PWR-SMP400BNC	16-pin PWR PDIP	0 to 70°C
PWR-SMP400BNI	16-pin PWR PDIP	-40 to 85°C
PWR-SMP400SRI	20-pin PWR SOIC	-40 to 85°C





## PWR-SMP400 Functional Description

### Pre-regulator and On-board Voltages

The pre-regulator provides the bias current required by the controller and driver circuitry. The pre-regulator consists of a high voltage MOSFET, a gate bias current source, and an error amplifier. The error amplifier regulates  $V_s$  to approximately 5.6 volts by controlling the gate of the MOSFET.

The pre-regulator MOSFET dissipates significant amounts of power when supplying bias current. This dissipation is eliminated when the feedback winding and filter drives the  $V_{BIAS}$  pin above 8.25 volts. The pre-regulator is then cut off and internal bias current is supplied by the feedback circuit.

$V_s$  is the supply voltage for the controller and driver circuitry. An external bypass capacitor connected to  $V_s$  is required for filtering and reducing noise.

### Band Gap Reference

$V_{REF}$  is the 1.25 V reference voltage generated by the temperature compensated bandgap reference and buffer. This voltage is used for setting thresholds for the error amplifier, over temperature circuit, and current limit circuit.

### Oscillator

The oscillator is completely self-contained. An internal capacitor is alternately charged and discharged by switched constant current sources. The oscillator frequency can be lowered by adding additional capacitance at the  $C_{EXT}$  pin.

The voltage switch points are determined by hysteresis built into a comparator. The period of the waveform is determined by values of the current sources which set the rising and falling slopes of the sawtooth waveform. Maximum duty cycle is equal to the ratio of the charge time to the period. Clock and blanking signals are synthesized from the comparator output for use by the modulator.

### Error Amplifier

The error amplifier consists of a high performance operational amplifier with the non-inverting input connected to the internal bandgap reference voltage. The output of the error amplifier directly controls the duty cycle of the power switch.

The error amplifier output pin EAO is buffered so that external loads will not affect its output. The buffer has an offset voltage of around 2 V, and an output impedance of about 1.5 k $\Omega$ .

### Pulse Width Modulator

The pulse width modulator implements a voltage-mode control loop, and generates the digital driver signal which controls the power switch. The duty cycle of the driver signal will change as a function of input voltage and load. Increasing the duty cycle causes the power supply output voltage to go up. Conversely, decreasing the duty cycle causes the output voltage to go down. The pulse width modulator compares the control voltage (error amplifier output) with the sawtooth voltage generated by the oscillator to produce the required duty cycle. The transfer function is linear from zero to maximum duty cycle, providing a very wide dynamic range.

### OV/UV Lockout Protection

Undervoltage/Overvoltage Lockout disables the power switch when the input voltage is either too low or too high. A simple resistor divider to the UV/OV input will determine the voltage levels at which lockout occurs.

### Overtemperature Protection

Temperature protection is provided by a precision analog circuit that turns the power switch off when the junction gets too hot (typically 135°C). The device will automatically reset and turn back on again when the junction has cooled past the hysteresis temperature level.

### Current Limit Protection

The current limit sense consists of a current mirror on the power device and a sense resistor. The current mirror produces a current proportional to the drain current of the power switch. A sense voltage is generated by passing the mirror current through a sense resistor. This voltage is then compared to a reference voltage using an internal comparator.



## 5 W, 48 V DC-DC Converter with Feedback Winding Regulation

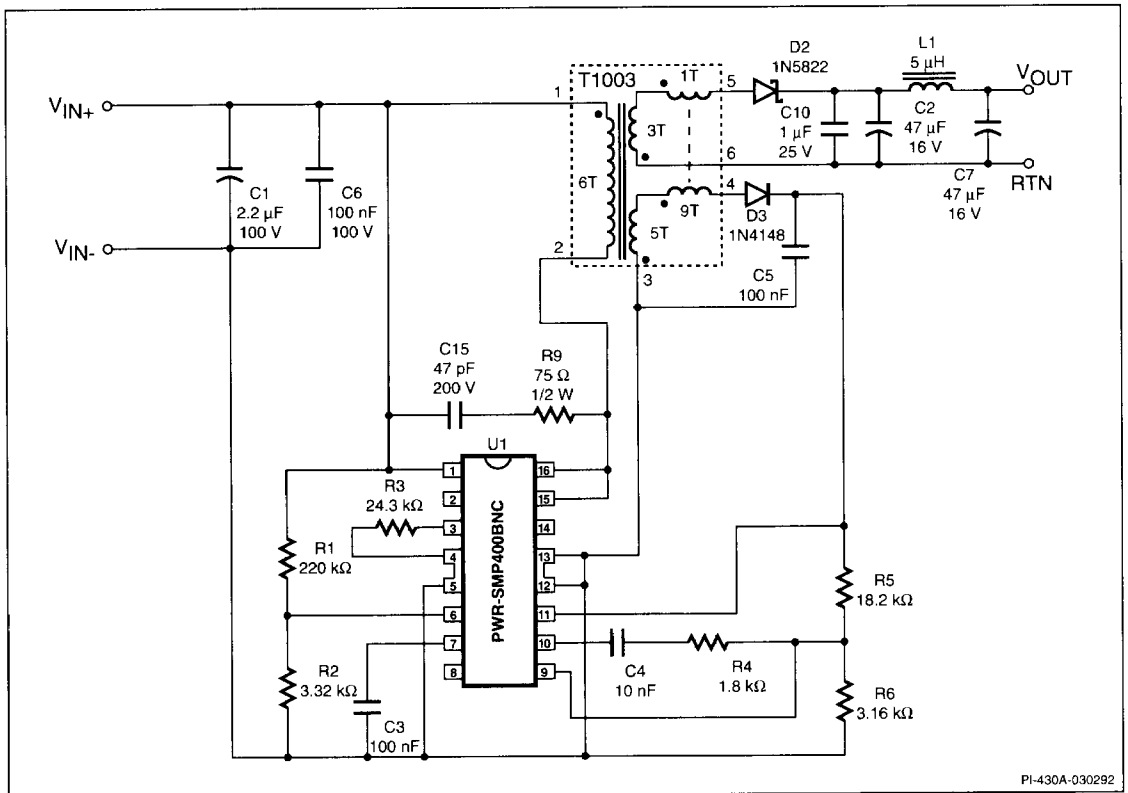


Figure 4. Schematic Diagram of a 5 W DC-DC Converter Utilizing the PWR-SMP400. For Improved Regulation, use the Optical Feedback Circuit Shown in AN-8.

### General Circuit Operation

The flyback power supply circuit shown in Figure 4, when operated with the T1003 standard transformer (see DA-3), will produce a 5 volt, 5 watt power supply that will operate from 30 to 80 VDC input voltage. The output voltage is selected by the turns ratio of the output winding to the feedback winding. The PWR-SMP400 has been designed for a feedback voltage (pin 11) of 8.5 volts. The effective transformer volts per turn can be fine tuned if necessary by the number of junctions in D3. The diode

D2 should be a Schottky rectifier to reduce diode switching losses. Three elements affect the regulation of the output voltage; maintaining a constant feedback winding voltage, tight coupling of the power transformer, and the use of a pulse transformer to cancel the leakage inductance voltage spike.

C1 and C6 form the EMI filter. The voltage divider formed by R1 and R2 set the input voltage that activates the input undervoltage and overvoltage shutdown

function. C15 and R9 damp the leakage inductance ringing voltage. C2, C7, C10 and L1 form the output filter. This damping network improves the regulation of the output voltage. R5 and R6 set the feedback voltage (VBIAS) to 8.5 volts. R4, R5, C2, C4, C7, and T1 determine the control loop frequency response. R3 sets the current sources within the PWR-SMP400. C3 and C5 are bypass capacitors.



## General Circuit Operation (cont.)

To achieve full output power and reliable operation of the PWR-SMP400, both DRAIN connections on the batwing DIP package (pin 15 and 16) must be connected together at the printed circuit board. Pin 15 and 16 are not connected within the package.

This circuit uses a secondary winding to monitor and regulate the output voltage. This technique can provide regulation and stability of  $\pm 5\%$ . If tighter regulation is required for a given application, an optical feedback technique can be used. See AN-8 for further information on optical feedback.

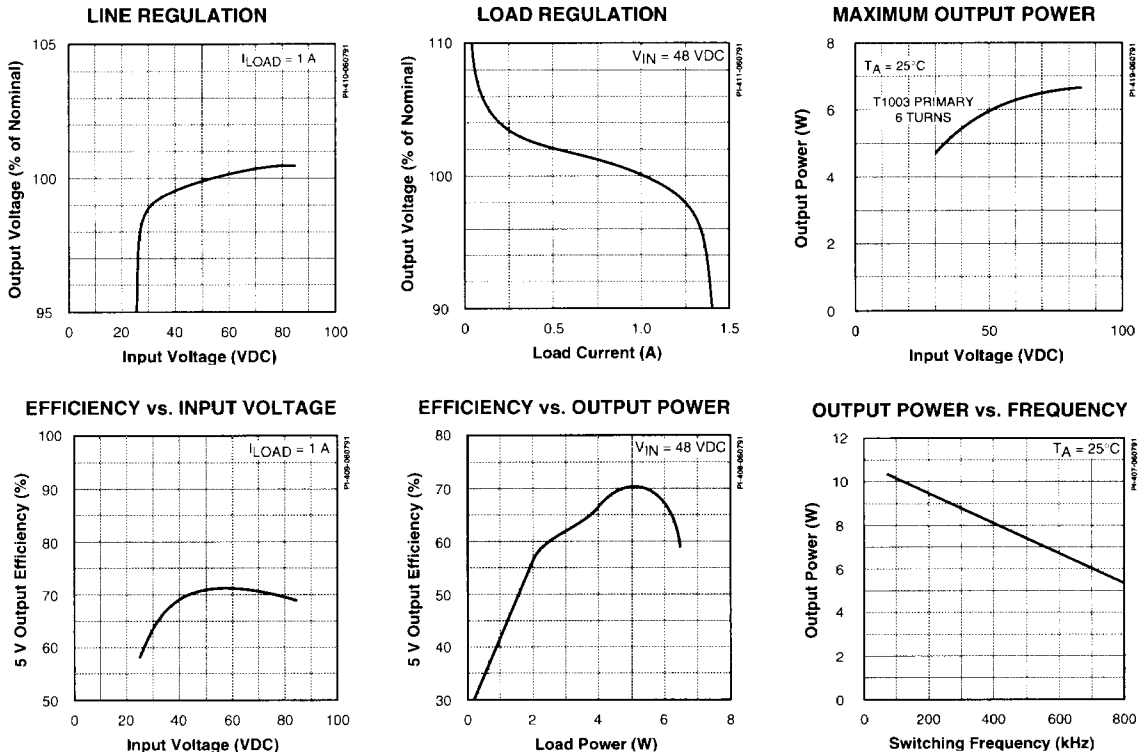
The circuit shown in Figure 4 is the schematic diagram of the PWR-EVAL4 evaluation board. This completely assembled and tested board can be ordered directly from Power Integrations, Inc. for evaluation of the PWR-SMP400. Complete supply specifications are included, as well as instructions on how to modify the board for other output voltages and oscillator frequencies.

The line and load regulation graphs shown below were measured on a PWR-EVAL4 board operated from a DC source. The switching frequency of the power supply was measured at 750 kHz.

The maximum output power curve shows the power output capability for the standard transformer T1003. See DA-3 for further information on ordering transformers for use with the PWR-SMP400.

The output power versus frequency curve was generated by characterization of the PWR-SMP400 at various frequencies. Several different power transformers, optimized for each frequency, were used to generate the maximum power at each point. The curves illustrate the trade-offs between AC and DC power losses within the device. As AC losses rise with frequency, DC losses and output power must be reduced to maintain the same device maximum power dissipation.

## Typical Performance Characteristics (Figure 4 Power Supply)



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**ABSOLUTE MAXIMUM RATINGS<sup>1</sup>**

Drain Voltage .....	200 V	Power Dissipation	
V <sub>IN</sub> Voltage .....	200 V	SR Suffix (T <sub>A</sub> = 25°C) .....	3.0 W
V <sub>BIAS</sub> Voltage .....	11 V	(T <sub>A</sub> = 70°C) .....	1.5 W
Drain Current <sup>(2)</sup> .....	2.5 A	Thermal Impedance (θ <sub>JA</sub> )(BN Suffix) .....	43°C/W
Input Voltage <sup>(3)</sup> .....	- 0.3 V to V <sub>S</sub> + 0.3 V	(SR Suffix) .....	30°C/W
Storage Temperature .....	-65 to 125°C	Thermal Impedance (θ <sub>JC</sub> ) <sup>(5)</sup> (BN Suffix) .....	6°C/W
Ambient Temperature (C Suffix) .....	0 to 70°C	(SR Suffix) .....	6°C/W
(I Suffix) .....	-40 to 85°C		
Junction Temperature <sup>(2)</sup> .....	150°C		
Lead Temperature <sup>(4)</sup> .....	260°C		
Power Dissipation			
BN Suffix (T <sub>A</sub> = 25°C) .....	2.1 W		
(T <sub>A</sub> = 70°C) .....	1.05 W		

1. Unless noted, all voltages referenced to COM.
2. Normally limited by internal circuitry.
3. Does not apply to V<sub>IN</sub> or DRAIN.
4. 1/16" from case for 5 seconds.
5. Measured at pin 12/13.

Specification	Symbol	Test Conditions, Unless Otherwise Specified: V <sub>IN</sub> = 48 V, V <sub>BIAS</sub> = 8.5 V, COM = 0 V R <sub>EXT</sub> = 24.3 kΩ T <sub>A</sub> = Full Operating Range (see Note 1)	Test Limits			Units	
			MIN	TYP	MAX		
<b>OSCILLATOR</b>							
Output Frequency	f <sub>OSC</sub>	C <sub>EXT</sub> = Open	C Suffix	650	750	825	kHz
			I Suffix	650	750	850	
<b>PULSE WIDTH MODULATOR</b>							
Duty Cycle	DC	C <sub>EXT</sub> = Open	0-35	0-40		%	
		f <sub>OSC</sub> = 200 kHz	0-45	0-50			
<b>CIRCUIT PROTECTION</b>							
Current Limit Threshold			0.9	1.1	1.25	A	
Input UV Trip-off			0.29	0.34	0.39	V	
Input UV Hysteresis			35	50	70	mV	
Input OV Trip-off		See Note 2	1.17	1.25	1.33	V	
Input OV Hysteresis			40	60	80	mV	
OV/UV Turn-off Delay Time		See Figure 5		250	500	ns	



Specification	Symbol	Test Conditions, Unless Otherwise Specified: $V_{IN} = 48\text{ V}$ , $V_{BB} = 8.5\text{ V}$ , $COM = 0\text{ V}$ $R_{EXT} = 24.3\text{ k}\Omega$ $T_A = \text{Full Operating Range (see Note 1)}$	Test Limits			Units
			MIN	TYP	MAX	
<b>CIRCUIT PROTECTION (cont.)</b>						
Thermal Shutdown Temperature			115	135		$^{\circ}\text{C}$
Thermal Shutdown Hysteresis				45		$^{\circ}\text{C}$
<b>ERROR AMPLIFIER</b>						
Reference Voltage	$V_{REF}$		1.21	1.25	1.29	V
Reference Voltage Temperature Drift	$\Delta V_{REF}$			50		ppm/ $^{\circ}\text{C}$
Gain-Bandwidth Product			0.9	1.0		MHz
DC Gain	$A_{VOL}$		60	80		dB
Output Impedance	$Z_{OUT}$			1.5		$\text{k}\Omega$
<b>OUTPUT</b>						
ON-State Resistance	$R_{DS(ON)}$	$I_D = 500\text{ mA}$	$T_J = 25^{\circ}\text{C}$ $T_J = 115^{\circ}\text{C}$	3 5.3	4.1 6.4	$\Omega$
ON-State Current	$I_{D(ON)}$	$V_{DS} = 10\text{ V}$		0.9	1.1	A
OFF-State Current	$I_{DSS}$	$V_{DRAIN} = 160\text{ V}$ , $T_A = 115^{\circ}\text{C}$		10	25	$\mu\text{A}$
Breakdown Voltage	$BV_{DSS}$	$I_D = 100\ \mu\text{A}$ , $T_A = 25^{\circ}\text{C}$	200			V
Output Capacitance	$C_{OSS}$	$V_{DRAIN} = 25\text{ V}$ , $f = 1\text{ MHz}$		75		pF
Output Stored Energy	$E_{OSS}$	$V_{DRAIN} = 48\text{ V}$		85		nJ
Rise Time	$t_R$	See Figure 5		10	20	ns

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Specification	Symbol	Test Conditions, Unless Otherwise Specified: $V_{IN} = 48\text{ V}$ , $V_{BIAS} = 8.5\text{ V}$ , $COM = 0\text{ V}$ $R_{EXT} = 24.3\text{ k}\Omega$ $T_A = \text{Full Operating Range (see Note 1)}$		Test Limits			Units
				MIN	TYP	MAX	
<b>OUTPUT (cont.)</b>							
Fall Time	$t_F$	See Figure 5			20	50	ns
<b>SUPPLY</b>							
Pre-regulator Voltage	$V_{IN}$			20		200	V
Pre-regulator Cutoff Voltage	$V_{BIAS(CO)}$			6.5		8.25	V
Off-line Supply Current	$I_{IN}$	$V_{BIAS}$ not connected, $C_{EXT} = \text{Open}$	C Suffix		4	5.0	mA
			I Suffix		4	5.6	
		$V_{BIAS} > 8.25\text{ V}$				0.1	
$V_{BIAS}$ Supply Voltage	$V_{BIAS}$	$V_{BIAS}$ externally supplied via feedback		8.25		9.0	V
$V_{BIAS}$ Supply Current	$I_{BIAS}$	$V_{BIAS}$ externally supplied via feedback	C Suffix		4	5.0	mA
			I Suffix		4	5.6	
$V_S$ Source Voltage	$V_S$			5.1		6.0	V
$V_S$ Source Current	$I_S$					400	$\mu\text{A}$

**NOTES:**

- Those specifications having only one limit number apply over the entire temperature range for both C Suffix (0 to 70°C), and I Suffix (-40 to 85°C) versions. Those specifications with a split limit showing each temperature range separately are as marked.
- Applying >3.5 V to the OV/UV pin activates an internal test circuit that turns on the output switch continuously. Destruction of the part can occur if the output of the PWR-SMP400 is connected to a high voltage power source when the test circuit is activated.





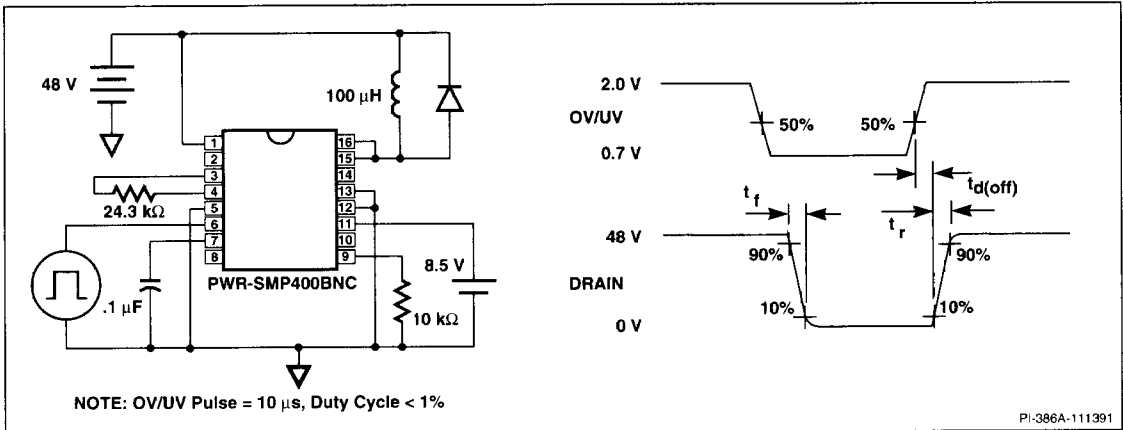
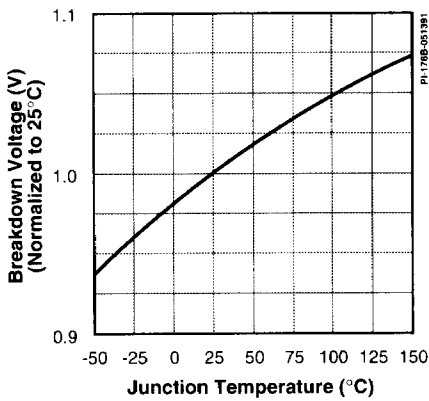
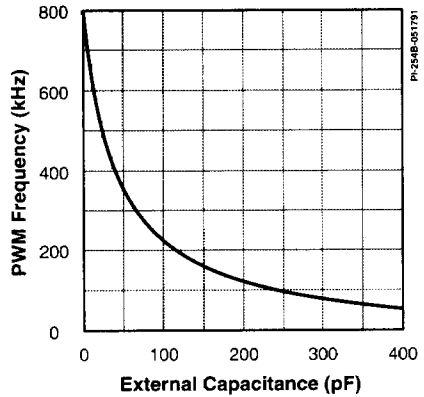


Figure 5. Switching Time Test Circuit.

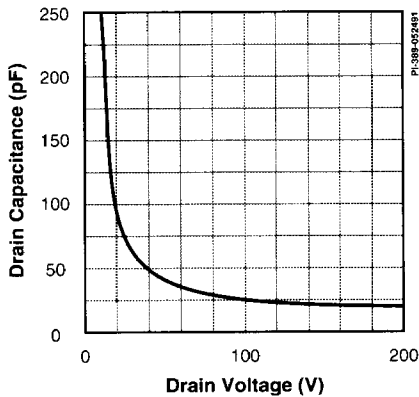
**BREAKDOWN vs. TEMPERATURE**



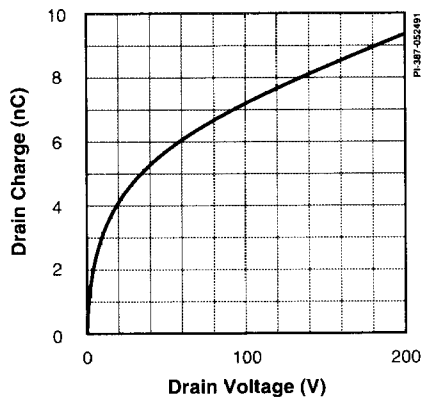
**f<sub>PWM</sub> vs. EXTERNAL CAPACITANCE**



**C<sub>oss</sub> vs. DRAIN VOLTAGE**



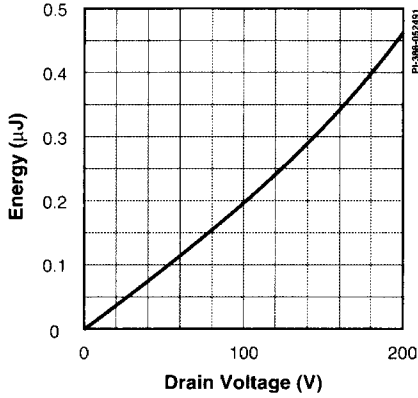
**DRAIN CHARGE vs. DRAIN VOLTAGE**



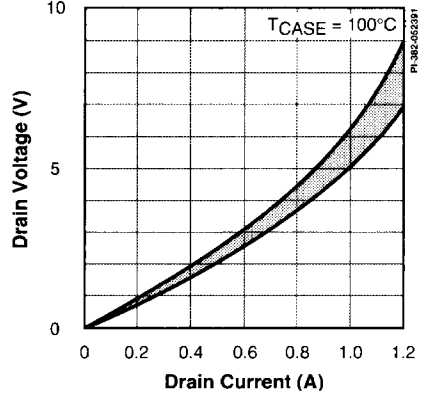
1



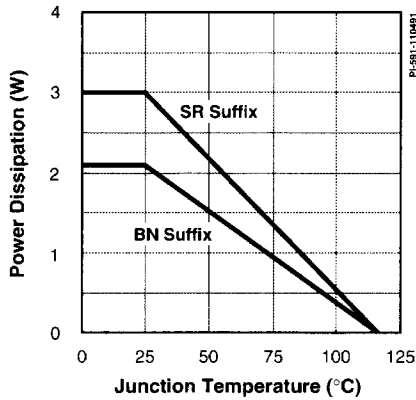
**DRAIN CAPACITANCE ENERGY**



**TRANSFER CHARACTERISTICS**



**PACKAGE POWER DERATING**



**TRANSIENT THERMAL IMPEDANCE**

